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Supplementary Materials

High-Efficiency $CsPbBr_3$ Light-Emitting Diodes using One-Step Spin-Coating In Situ Dynamic Thermal Crystallization

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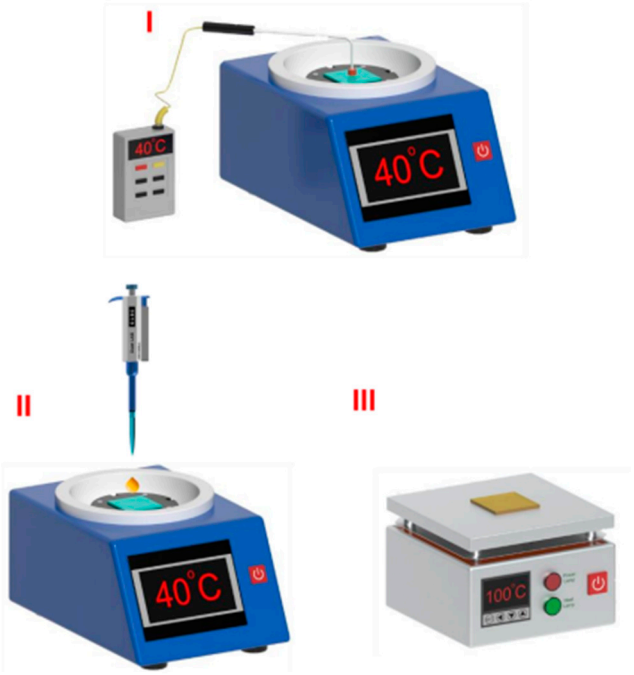

Figure S1. The fabrication process of one-step spin-coating in-situ thermally assisted crystallization process.

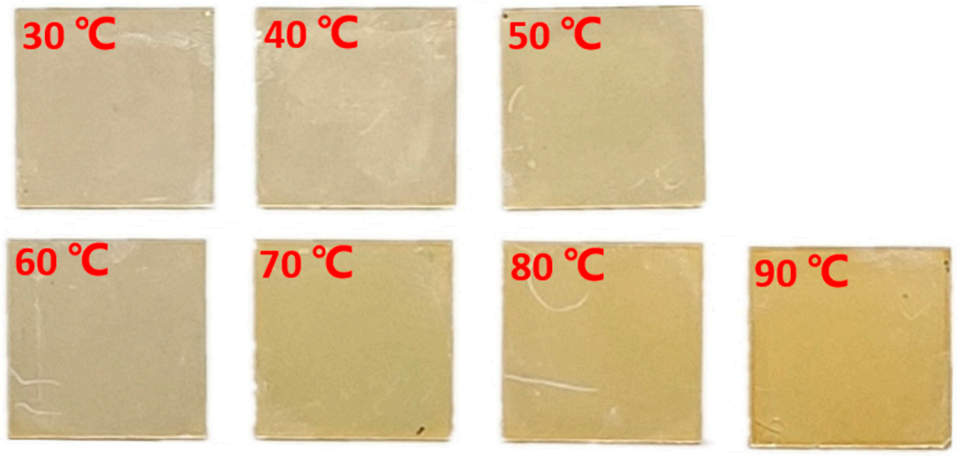

Figure S2. The color variation of perovskite film at different in situ heat-assisted crystallization temperatures.

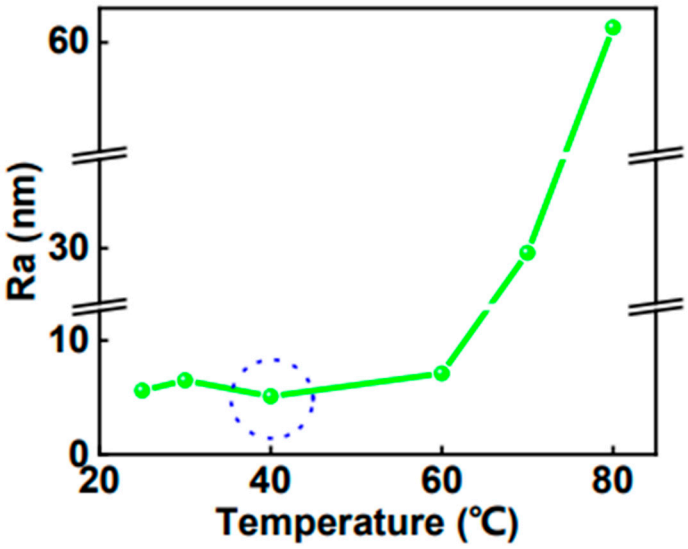

Figure S3. The roughness variation of perovskite film under different annealing temperature.

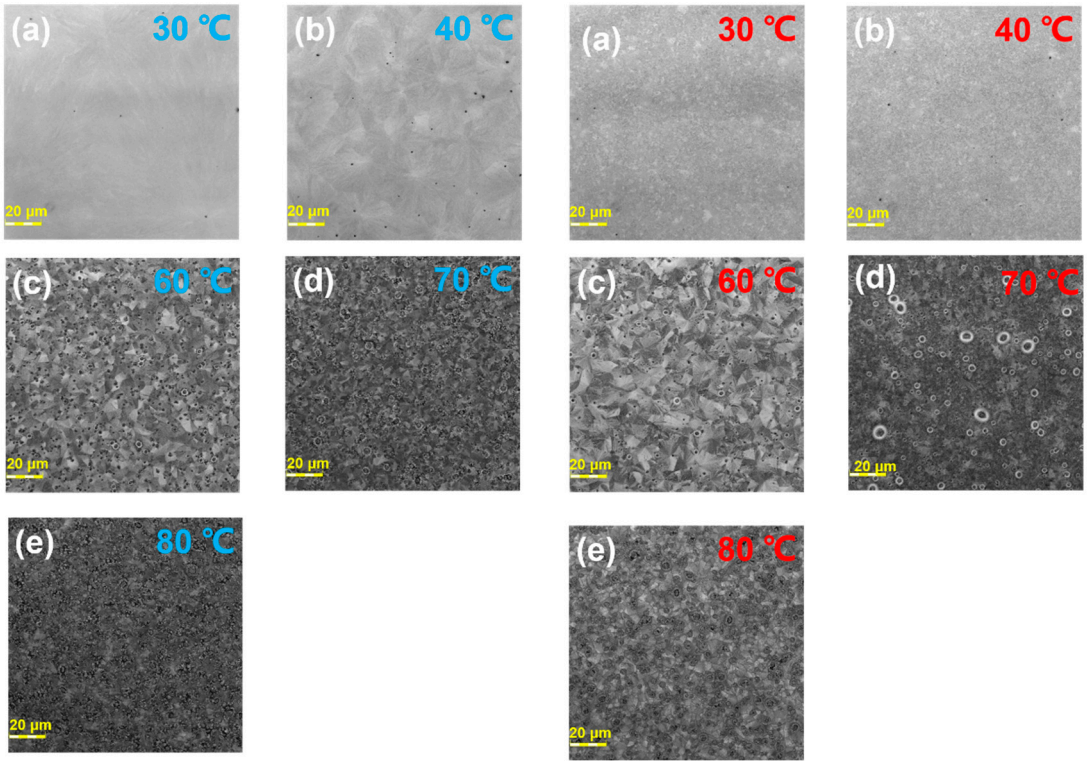

Figure S4. The laser confocal micrographs of unannealed and annealed $CsPbBr_3$ films at different in situ thermally assisted crystallization temperatures.

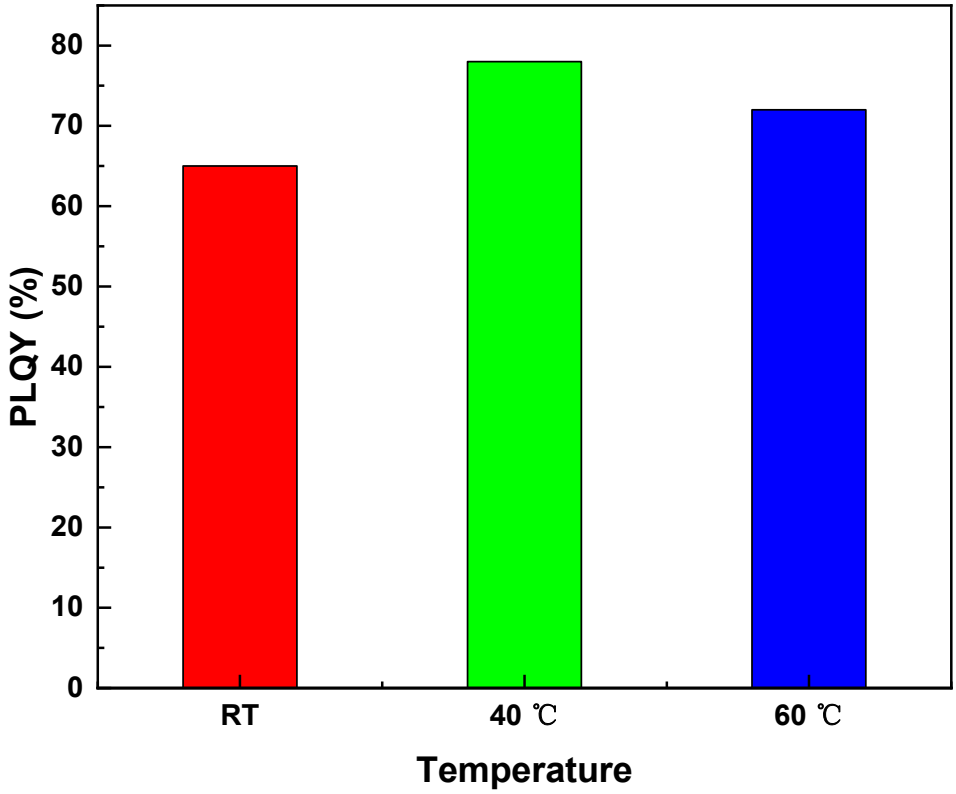

Figure S5. PLQY measurement of the perovskite film under different annealing temperature.

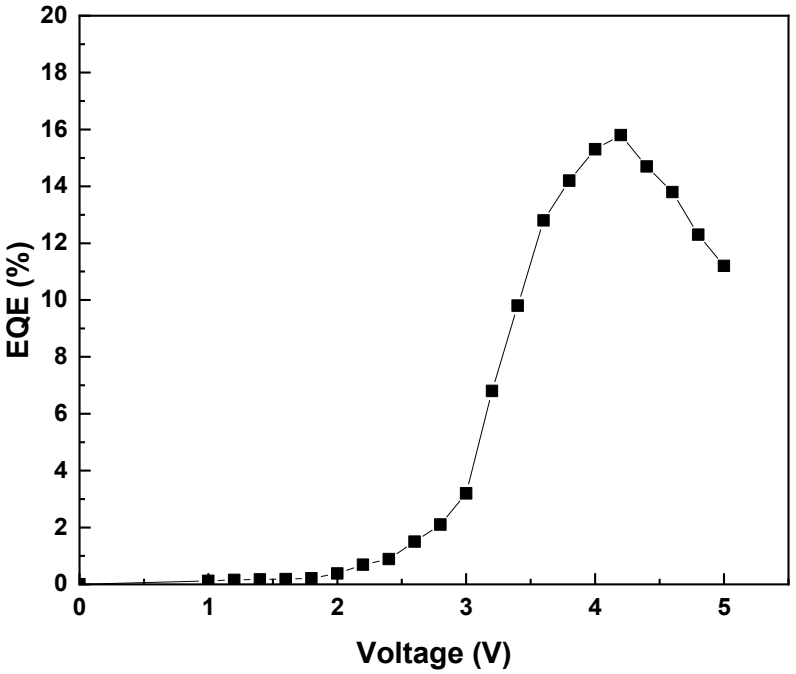

Figure S6. EQE measurement for the best performance PeLED device.

Table S1. The concentration of elements in the perovskite film.

Element	Percentage
Cs	35.36%
Pb	8.22 %
Br	56.42 %